

# **PBSS5350TVL Datasheet**



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DiGi Electronics Part Number PBSS5350TVL-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBSS5350TVL

Description PBSS5350T/SOT23/TO-236AB

**Detailed Description** Bipolar (BJT) Transistor PNP 50 V 2 A 100MHz Surfac

e Mount TO-236AB



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PBSS5350TVL	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	2 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
50 V	390mV @ 300mA, 3A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	200 @ 1A, 2V
Frequency - Transition:	Operating Temperature:
100MHz	150°C (TJ)
Mounting Type:	Package / Case:
Surface Mount	TO-236-3, SC-59, SOT-23-3
Supplier Device Package:	Base Product Number:
TO-236AB	PBSS5350

# **Environmental & Export classification**

8541.29.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



# **PBSS5350T**

# 50 V, 3 A PNP low VCEsat transistor

1 January 2023

**Product data sheet** 

### 1. General description

PNP low  $V_{CEsat}$  transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350T

#### 2. Features and benefits

- Low collector-emitter saturation voltage  $V_{\text{CEsat}}$  and corresponding low  $R_{\text{CEsat}}$
- · High collector current capability
- High collector current gain
- · Improved efficiency due to reduced heat generation

## 3. Applications

- Power management applications
- · Low and medium power DC/DC converters
- Supply line switching
- Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
I <sub>C</sub>	collector current		-	-	-2	Α
I <sub>CRM</sub>		$\delta \leq 0.25$ ; Operated under pulsed conditions; $t_p \leq 100$ ms	-	-	-3	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	90	135	mΩ



50 V, 3 A PNP low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	]3	
2	E	emitter		C
3	С	collector		В
				) E
			SOT23	sym132

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS5350T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS5350T	ZD%

[1] % = placeholder for manufacturing site code

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### 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
Ic	collector current			-	-2	А
I <sub>CRM</sub>	repetitive peak collector current	$\delta \le 0.25$ ; Operated under pulsed conditions; $t_p \le 100 \text{ ms}$		-	-3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	А
I <sub>B</sub>	base current			-	-0.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[4]	-	500	mW
			[1] [5]	-	1.2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width tp  $\leq$  100 ms, duty cycle  $\delta \leq$  0.25.

#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance from	in free air [	[1]	-	-	417	K/W
	[2]	[2]	-	-	260	K/W	
		[3]	[3]	-	-	230	K/W
			[4]	-	-	250	K/W
		[1] [5]	-	-	104	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$

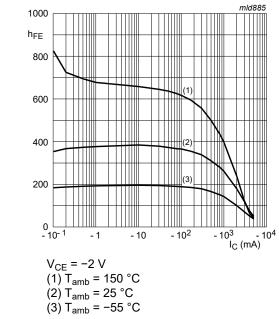
50 V, 3 A PNP low VCEsat transistor

### 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_E = -100 \ \mu\text{A}; \ I_C = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	-6	-	-	V
I <sub>СВО</sub>	collector-base cut-off	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	130	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -3 A; pulsed; t <sub>p</sub> ≤ 300 µs; T <sub>amb</sub> = 25 °C	80	-	-	
V <sub>CEsat</sub>	/ <sub>CEsat</sub> collector-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C	-	-	-90	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-180	mV
		$I_C$ = -2 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-320	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-270	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-390	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	90	135	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_C$ = -2 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.1	V
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.2	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	35	pF

#### 50 V, 3 A PNP low VCEsat transistor



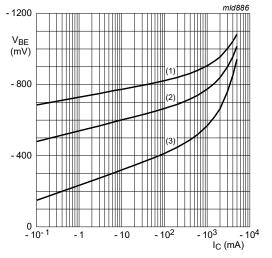
$$V_{CE} = -2 V$$

$$(1) T_{amb} = 150 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 1. DC current gain as a function of collector current; typical values



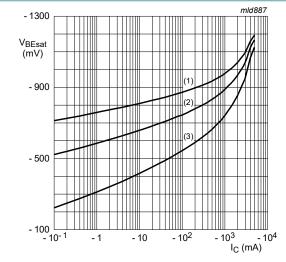
$$V_{CF} = -2 V$$

$$(1) T_{amb} = -55 °C$$

$$V_{CE} = -2 V$$
  
(1)  $T_{amb} = -55 °C$   
(2)  $T_{amb} = 25 °C$ 

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 2. Base-emitter voltage as a function of collector current; typical values



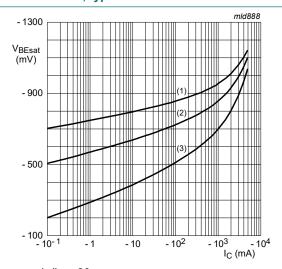
$$I_{\rm C}/I_{\rm B}=10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

$$(2) T_{amb} = 25 °C$$

$$(3) T_{amb} = 150 °C$$

Fig. 3. Base-emitter saturation voltage as a function of | Fig. 4. collector current; typical values



$$I_C/I_B = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Base-emitter saturation voltage as a function of collector current; typical values

#### 50 V, 3 A PNP low VCEsat transistor

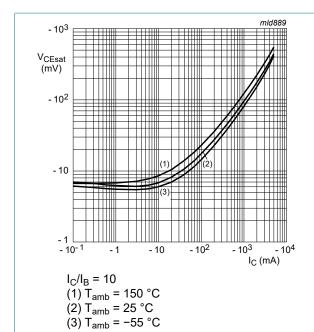
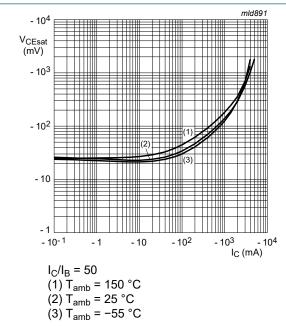
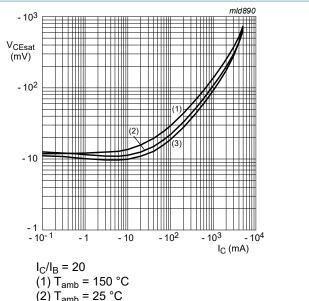


Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

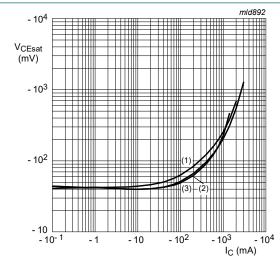


Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values



(1)  $T_{amb} = 150 \text{ °C}$ (2)  $T_{amb} = 25 \text{ °C}$ (3)  $T_{amb} = -55 \text{ °C}$ 

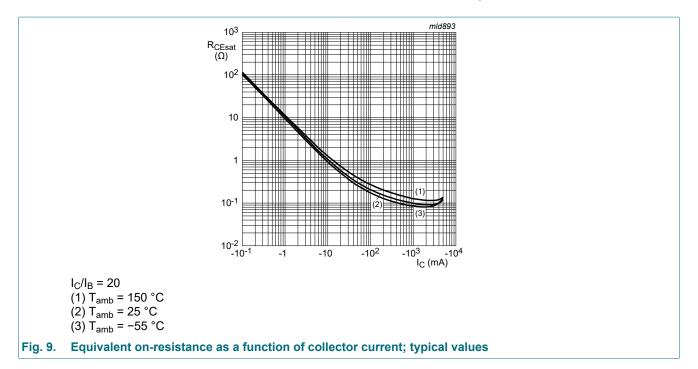
Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values



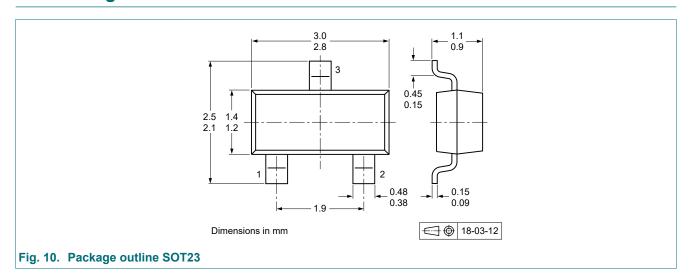
 $I_{\rm C}/I_{\rm B} = 100$ (1)  $T_{amb} = 150 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

#### 50 V, 3 A PNP low VCEsat transistor

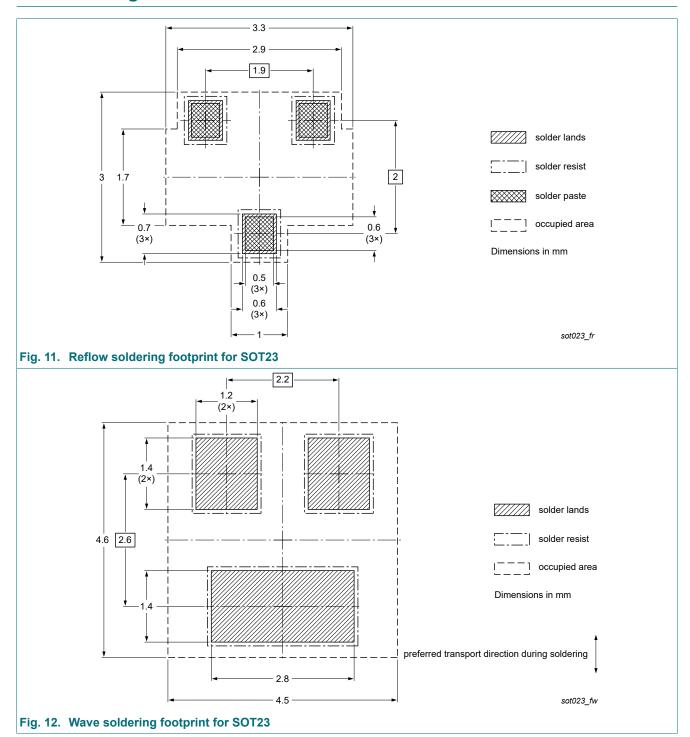


### 11. Package outline



50 V, 3 A PNP low VCEsat transistor

# 12. Soldering



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# 13. Revision history

#### Table 8. Revision history

table of Nevision History							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS5350T v.4	20230101	Product data sheet	-	PBSS5350T v.3			
Modifications:		<ul> <li>Product changed to non-automotive qualification. Please refer to nexperia.com for automotive(-Q) product alternative(s).</li> </ul>					
PBSS5350T v.3	20220510	Product data sheet	-	PBSS5350T v.2			
PBSS5350T v.2	20040113	Product data sheet	-	PBSS5350T v.1			
PBSS5350T v.1	20020808	Product data sheet	-	-			

#### 50 V, 3 A PNP low VCEsat transistor

### 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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